## **TOSHIBA**

# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## MICROWAVE POWER GaAs FET TIM7179-30UL

#### **FEATURES**

- HIGH POWER
  P1dB=45.0 dBm at 7.1GHz to 7.9GHz
- BROAD BAND INTERNALLY MATCHED FET
- HIGH GAIN
  G1dB=8.5dB at 7.1GHz to 7.9GHz
- **HERMETICALLY SEALED PACKAGE**

#### RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	44.0	45.0	
Compression Point						
Power Gain at 1dB Gain	G1dB	VDS= 10V	dB	7.5	8.5	
Compression Point		IDSset=6.4A				
Drain Current	IDS1	f = 7.1 to 7.9GHz	Α		7.0	8.0
Gain Flatness	ΔG		dB			±0.6
Power Added Efficiency	ηadd		%	_	39	_
3rd Order Intermodulation	IM3	Two-Tone Test	dBc	-44	-47	_
Distortion		Po=34.0 dBm				
Drain Current	IDS2	(Single Carrier Level)	Α	_	7.0	8.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C			100

Recommended gate resistance(Rg) : Rg= 28  $\Omega$ (MAX.)

### **ELECTRICAL CHARACTERISTICS** (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	mS		8000	_
		IDS= 10.0A				
Pinch-off Voltage	VGSoff	VDS= 3V	V	-0.5	-2.0	-3.0
		IDS= 80mA				
Saturated Drain Current	IDSS	VDS= 3V	Α	_	16.0	
		VGS= 0V				
Gate-Source Breakdown	VGSO	IGS=-240μA	V	-5	_	_
Voltage						
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.5

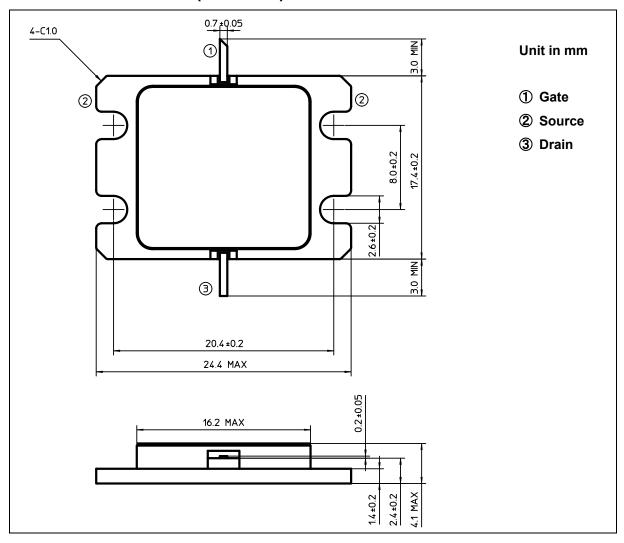
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## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25 °C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

## PACKAGE OUTLINE (7-AA05A)



#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.